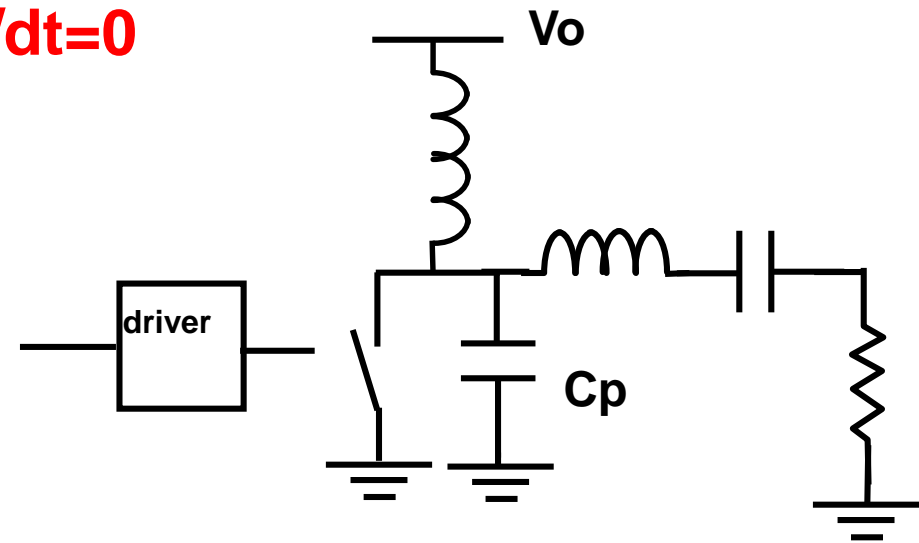
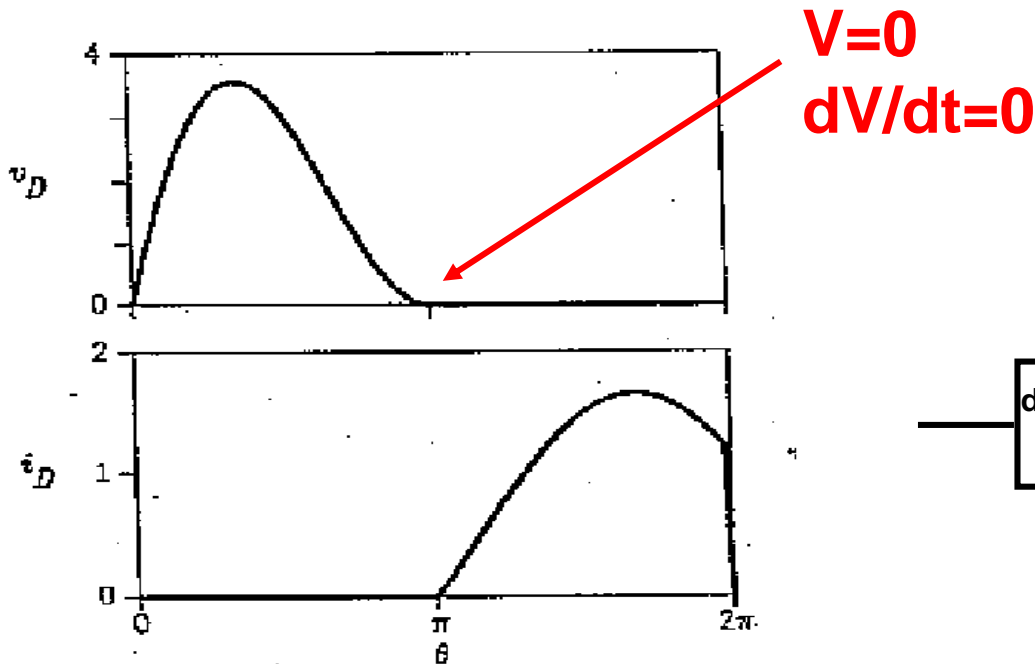




# Class E Amplifier

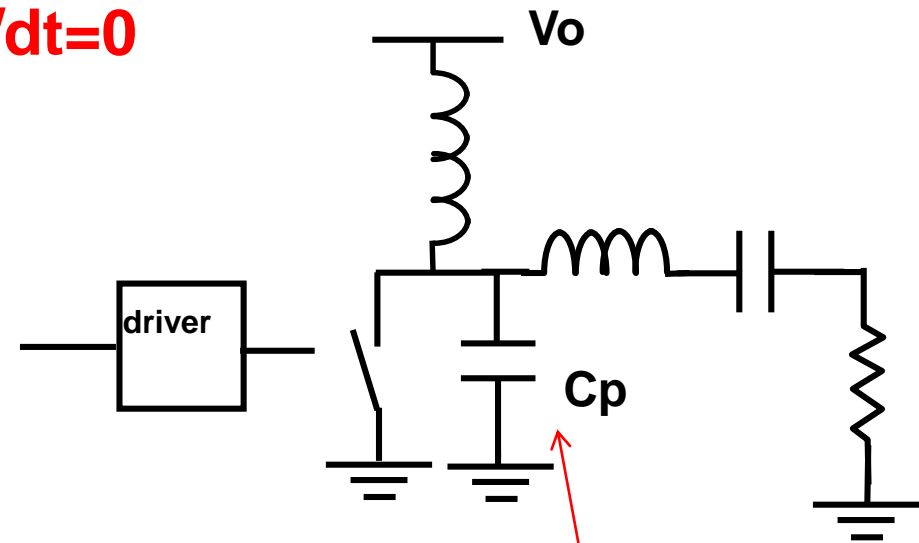
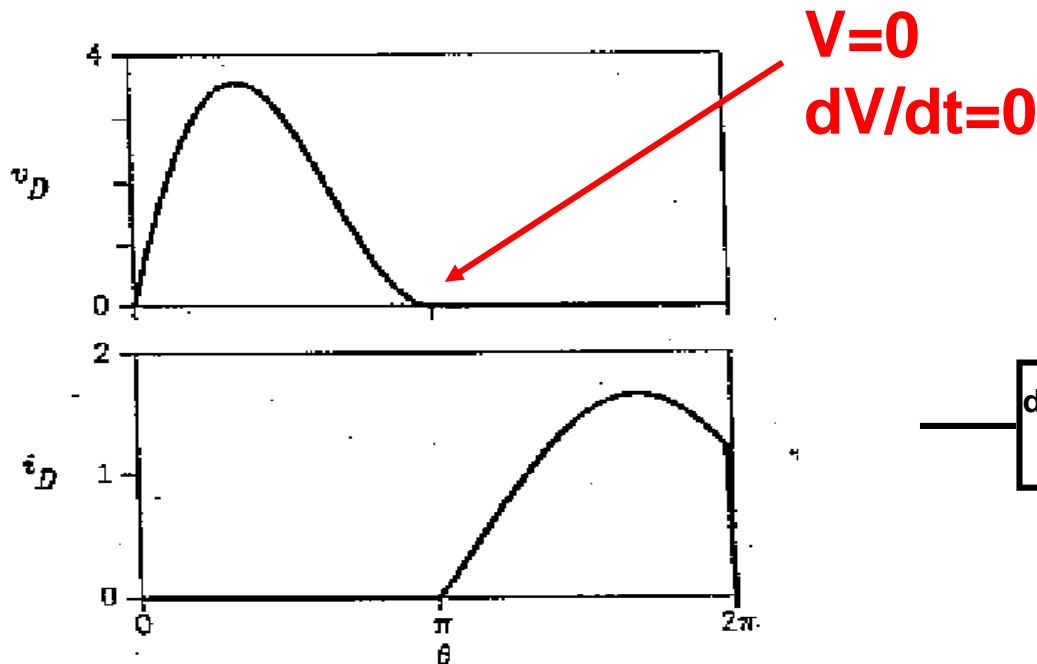
Clever resonant load is constructed so that  $V(t)=0$  when the switch closes!! This avoids  $1/2CV^2f$  loss.



- Voltage across switch is brought to zero when switch closes
- $dV/dt$  is also zero when switch closes. This makes operation relatively insensitive to rise time of input.

# Class E Amplifier

Clever resonant load is constructed so that  $V(t)=0$  when the switch closes!! This avoids  $1/2Cv^2f$  loss.

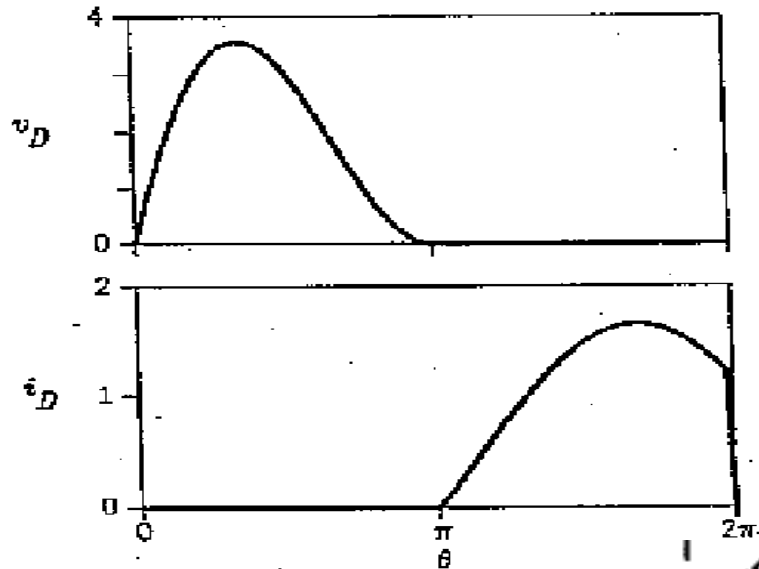


- Voltage across switch is brought to zero when switch closes
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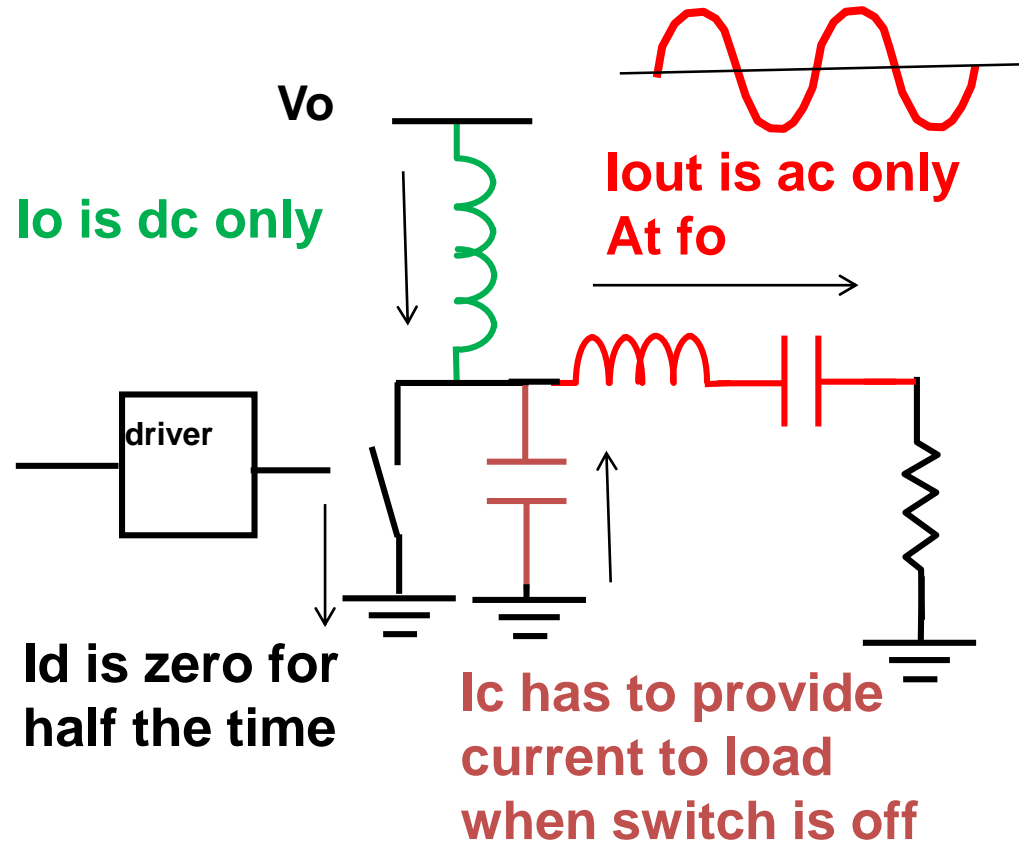
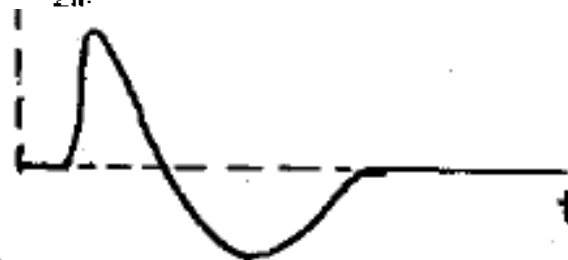
This is essential  
If device does not  
have enough  $C_d$ s  
then you must add  
this

# Class E Amplifier

- Load current is sinusoidal (just  $f_0$ ) due to filter
- Switch and capacitor provide current during different phases



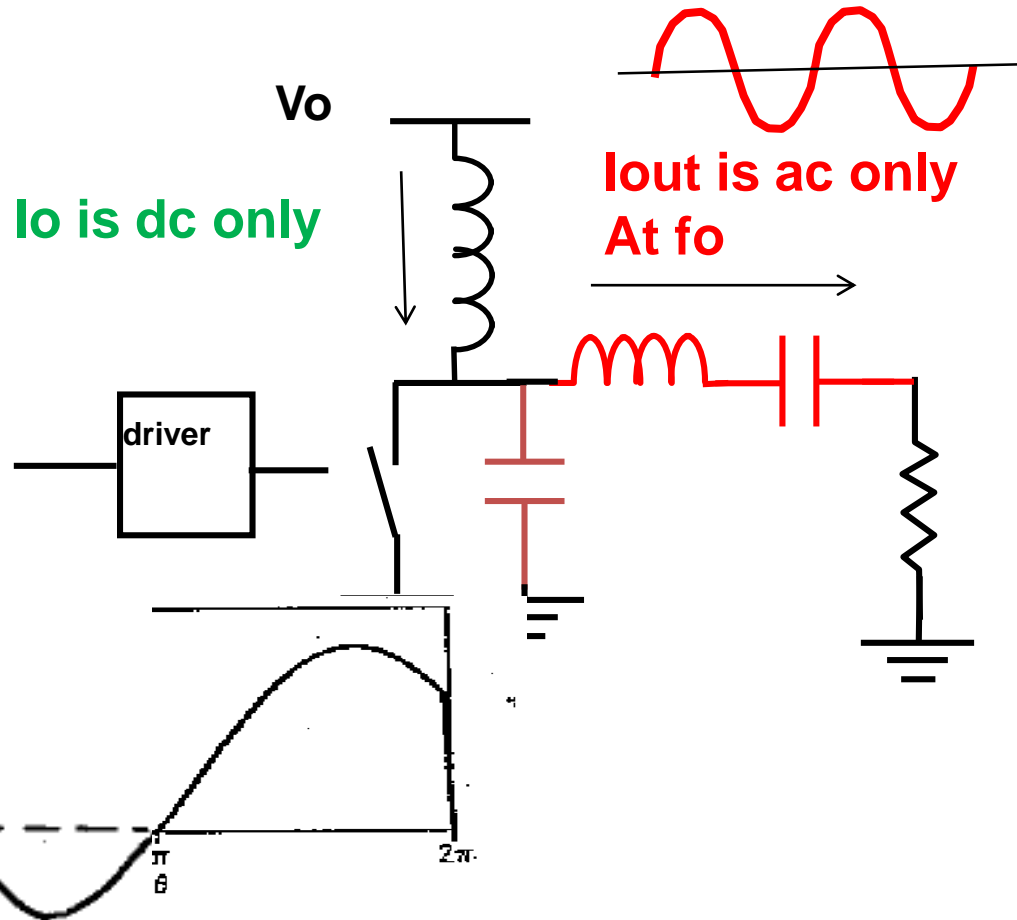
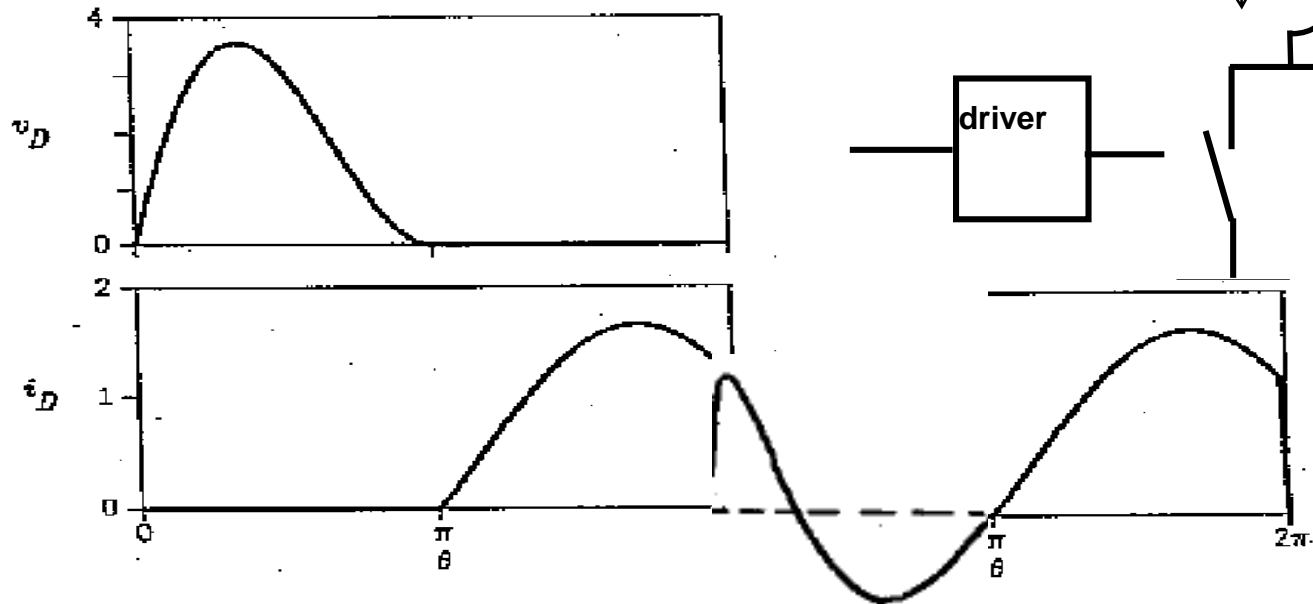
**Capacitor current**



# Class E Amplifier

- Load current is sinusoidal (just  $f_0$ ) due to filter

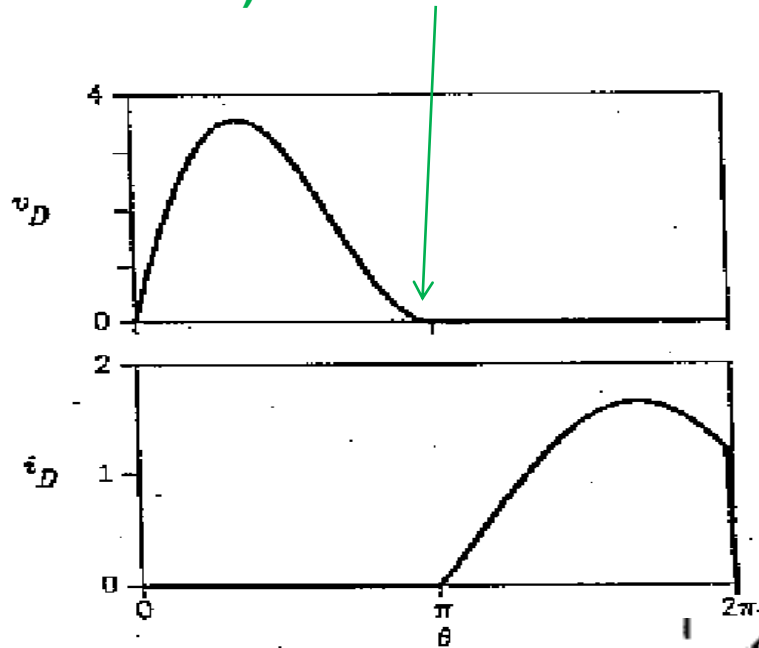
- Switch and capacitor provide current during different phases



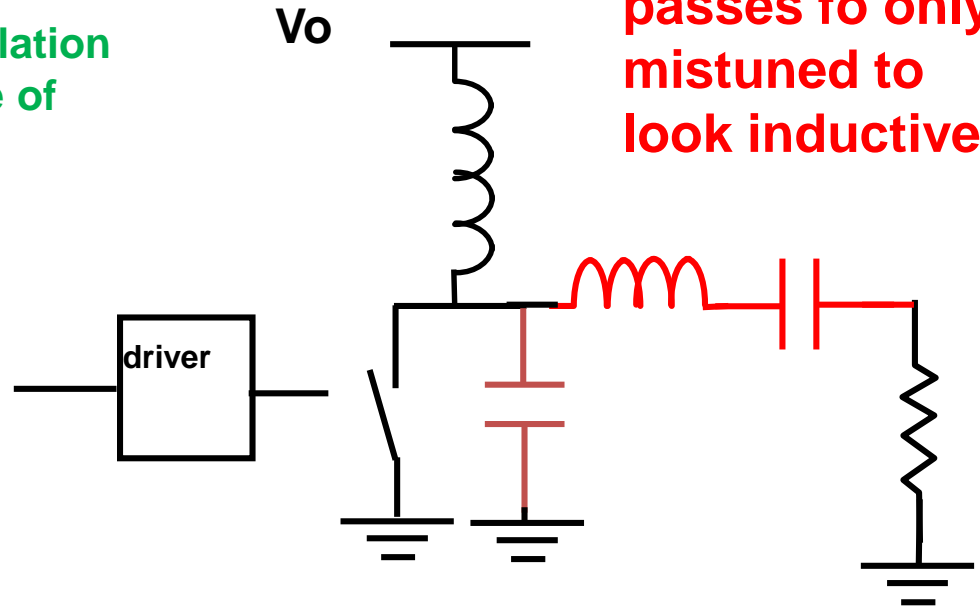
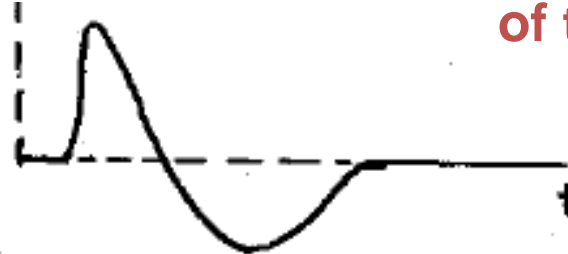
**Capacitor current**

# Class E Amplifier

$V=0$  and  $dV/dt=0$   
are achieved by carefully tuning  
Lextra of resonator,  $C_p$  and  $RL$  in relation  
operating frequency (and duty cycle of  
switch)



Capacitor current

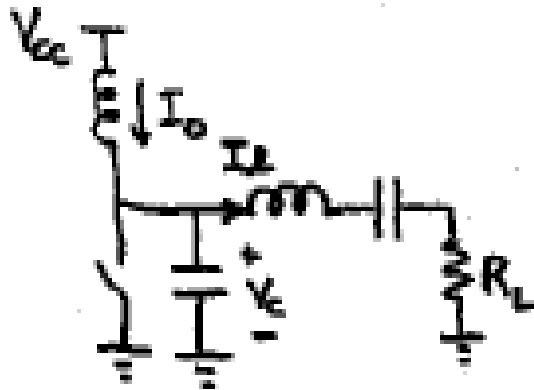


Filter that  
passes fo only;  
mistuned to  
look inductive

Capacitor  $C$  is often just  
the output capacitance  
of the switch

# Simple Analysis of Class E Amplifier

This is done in time domain!



Perfect choke :  $I_o = \text{constant}$

Perfect filter :  $I_L = -I_L \sin(\omega t + \phi)$

Calculate  $V_c(t)$  when switch is open

$$C \frac{dV_c}{dt} = I_o + I_L \sin(\omega t + \phi)$$

$$V_c(t) = \frac{I_o t}{C} - \frac{I_L}{\omega C} [\cos(\omega t + \phi) - \cos \phi]$$

Require  $V_c = 0$  at  $\omega t = \pi$  :

$$\frac{I_o \cdot \pi}{\omega C} - \frac{I_L}{\omega C} (-2 \cos \phi) = 0$$

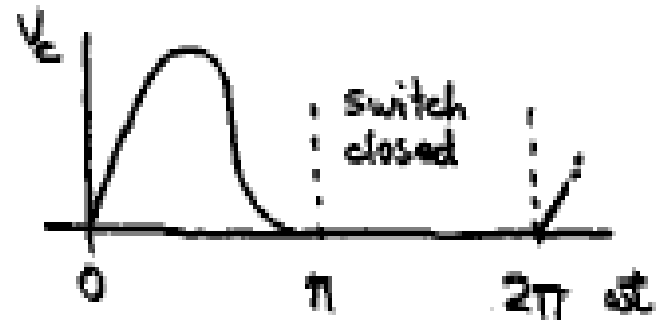
$$I_o = -\frac{2 I_L \cos \phi}{\pi}$$

Require  $\frac{dV_c}{dt} = 0$  at  $\omega t = \pi$  :

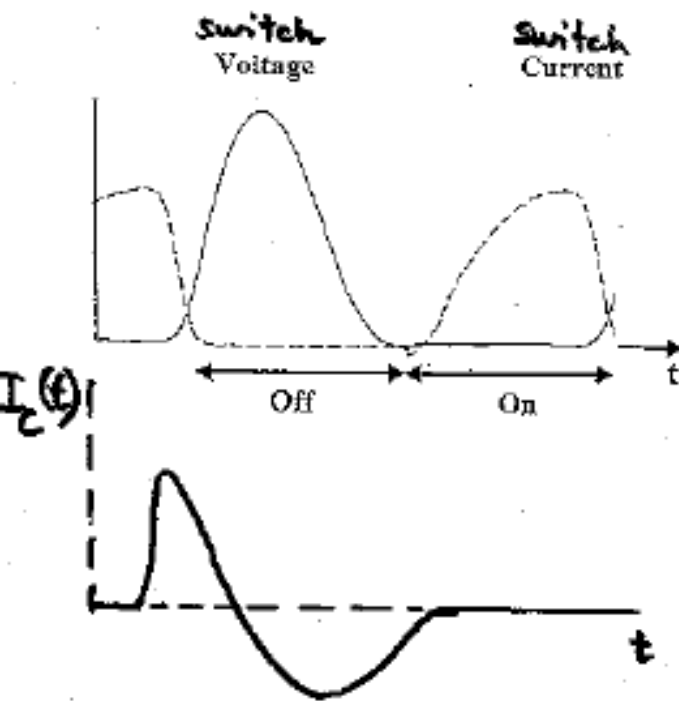
$$I_o + I_L \sin(\pi + \phi) = 0$$

$$I_o = I_L \sin \phi$$

$$-\frac{2}{\pi} = \frac{\sin \phi}{\cos \phi} = \tan \phi$$



# Class E Analysis (more)



$$V_c(t) = \frac{I_0 t}{C} - \frac{I_L}{\omega C} [\cos(\omega t + \phi) - \cos \phi] \quad t < \pi/\omega$$

$$I_0 + I_L \sin(\pi + \phi) = 0$$

$$I_0 = I_L \sin \phi$$

$$-\frac{2}{\pi} = \frac{\sin \phi}{\cos \phi} = \tan \phi$$

$$\phi = -32.5^\circ$$

$$I_L = 1.862 I_0$$

$$I_{\text{peak}} = 2.862 I_0$$

$$V_{cc}: \text{dc component of } V_c(t) = \frac{1}{\pi} \frac{I_0}{\omega C}$$

$$V_L: \text{Fourier component at } \omega \text{ of } V_c(t) = \frac{0.52 I_0}{\omega C}$$



$$Z_L = \underbrace{\frac{0.18}{\omega C}}_{R_L} + j \frac{0.21}{\omega C}$$

$$P_{\text{out}}(\omega) = \frac{1}{2} R_L I_L^2$$



## Class E Design Equations

---

$$Z_{out} = \frac{0.28015}{\omega C} e^{j49.0524^\circ} = \underbrace{\frac{0.18}{\omega C}}_{R_L} + j \frac{0.21}{\omega C} \quad \text{(for fundamental, after } C_p)$$

$$f_{opt} = \frac{I_{max}}{56.5 C V_d}$$

$$\eta_d = \frac{1 + (\pi/2 + \omega C R)^2}{1 + \pi^2/4 (1 + \pi \omega C R)^2}$$

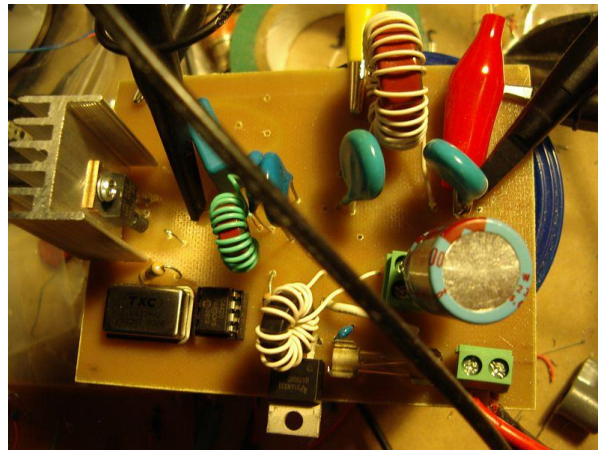
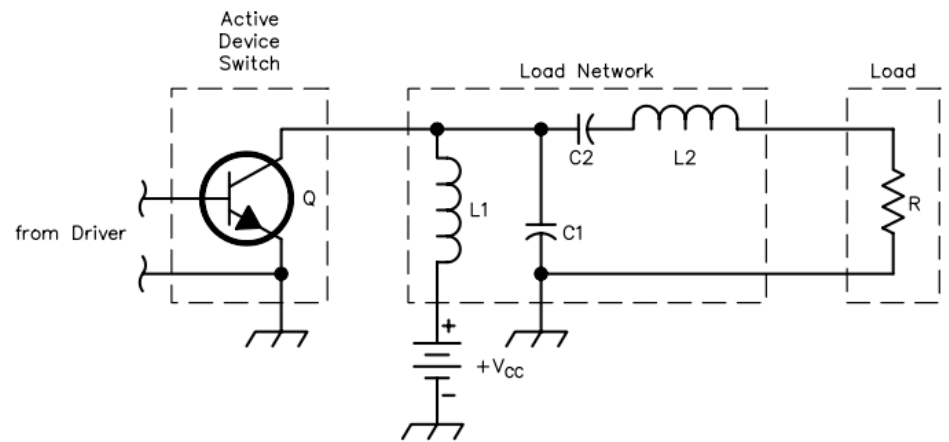
**Drain efficiency  
when on-  
resistance R is  
included**

## Class E Features

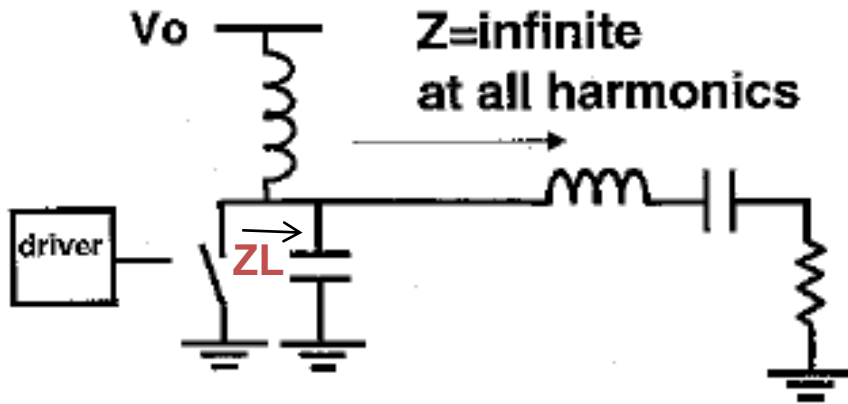
- **Efficiency is 100% (ideally) No dissipation in transistor**
- **If frequency changes, then  $V_{ce}$  does not quite go to 0 at switching instant  $\Rightarrow$  non-zero power dissipation due to  $C\Delta V^2$**
- **Amplitude of output depends on  $V_{cc}$  (not on input amplitude)**
- **$P_{out}$  at  $f_o = 0.78 * 1/8 * V_{max} I_{max}$  (lower than for Class A)**



**Nathan Sokal**



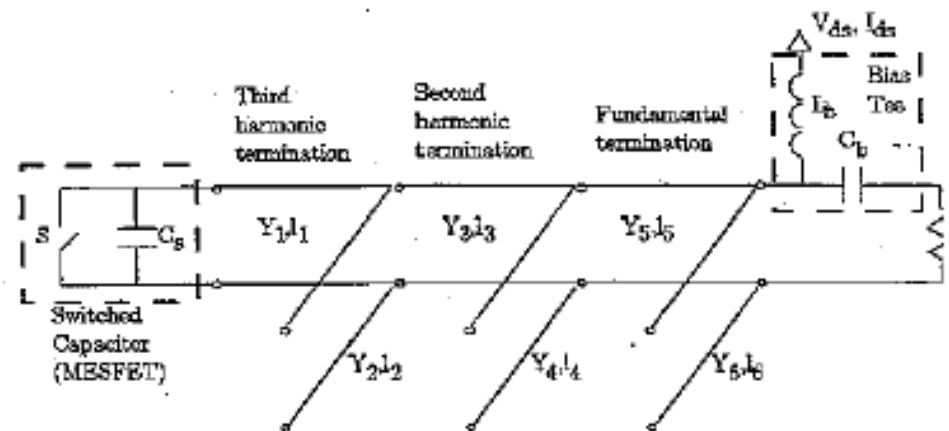
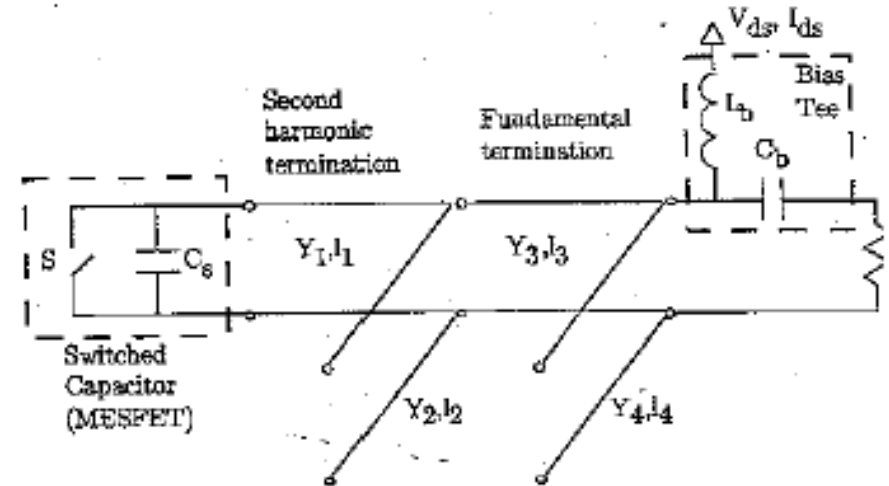
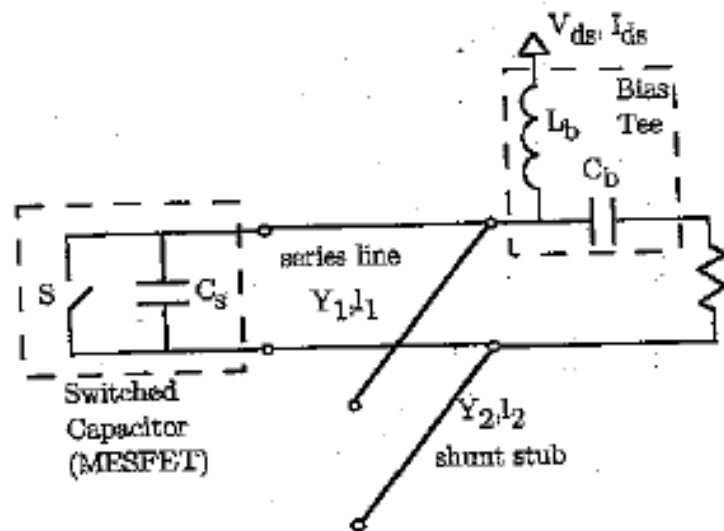
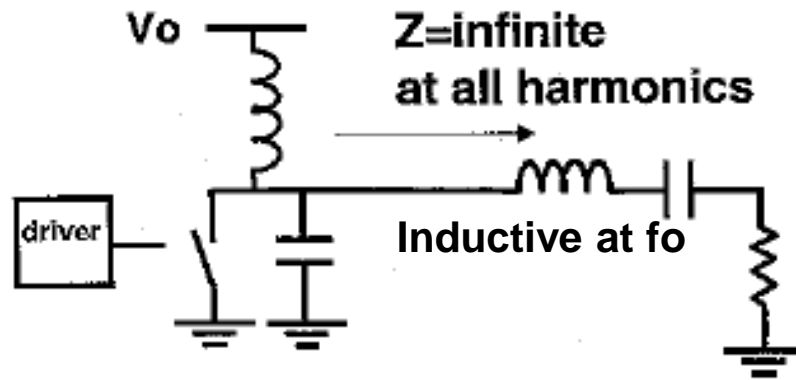
## Another Description of Class E



$$\begin{aligned} Z_L(f) &= R_L + jX_L \\ &\quad \text{with } X_L = +0.72 R_L \\ Z_L(2f) &= -jX_2 \\ &\quad \text{with } X_2 = 1.78 R_L \\ Z_L(3f) &= -jX_3 \\ &\quad \text{with } X_3 = 1.19 R_L \end{aligned}$$

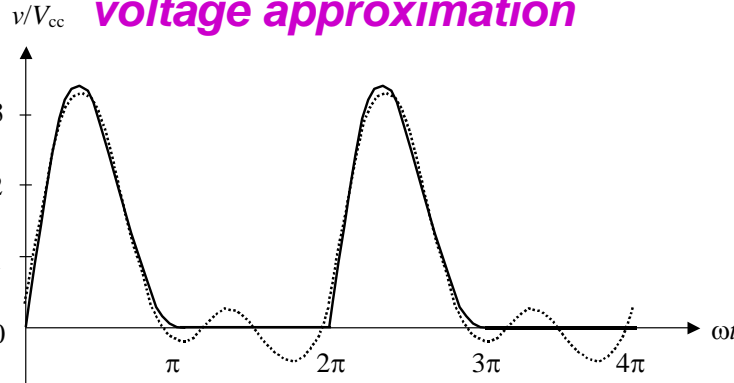
## Class E: Additional Implementations

Use transmission lines instead of lumped elements



# Class E with transmission lines: approximation

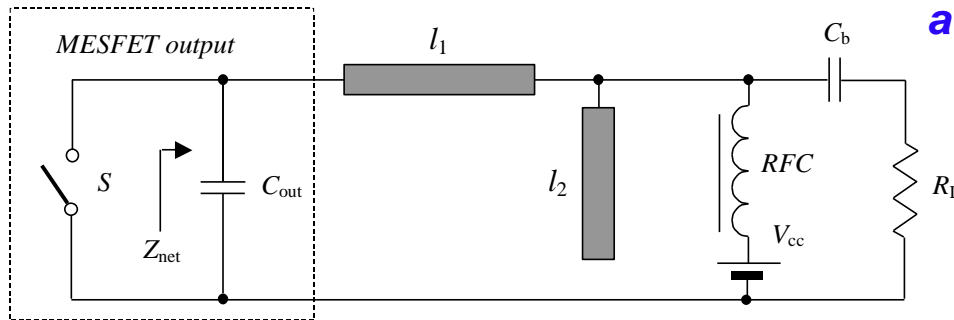
## Two-harmonic collector voltage approximation



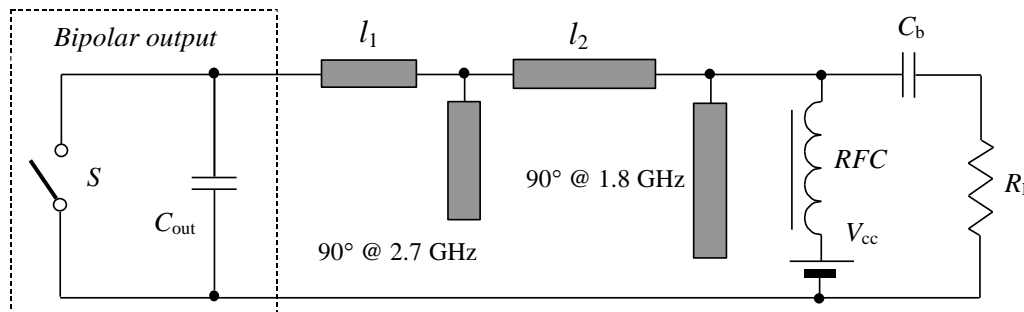
Optimum impedance at fundamental seen by device :

$$Z_{\text{net1}} = R \left( 1 + j \tan 49.052^\circ \right)$$

- electrical lengths of transmission lines  $l_1$  and  $l_2$  should be of  $45^\circ$  to provide open circuit seen by device at second harmonic



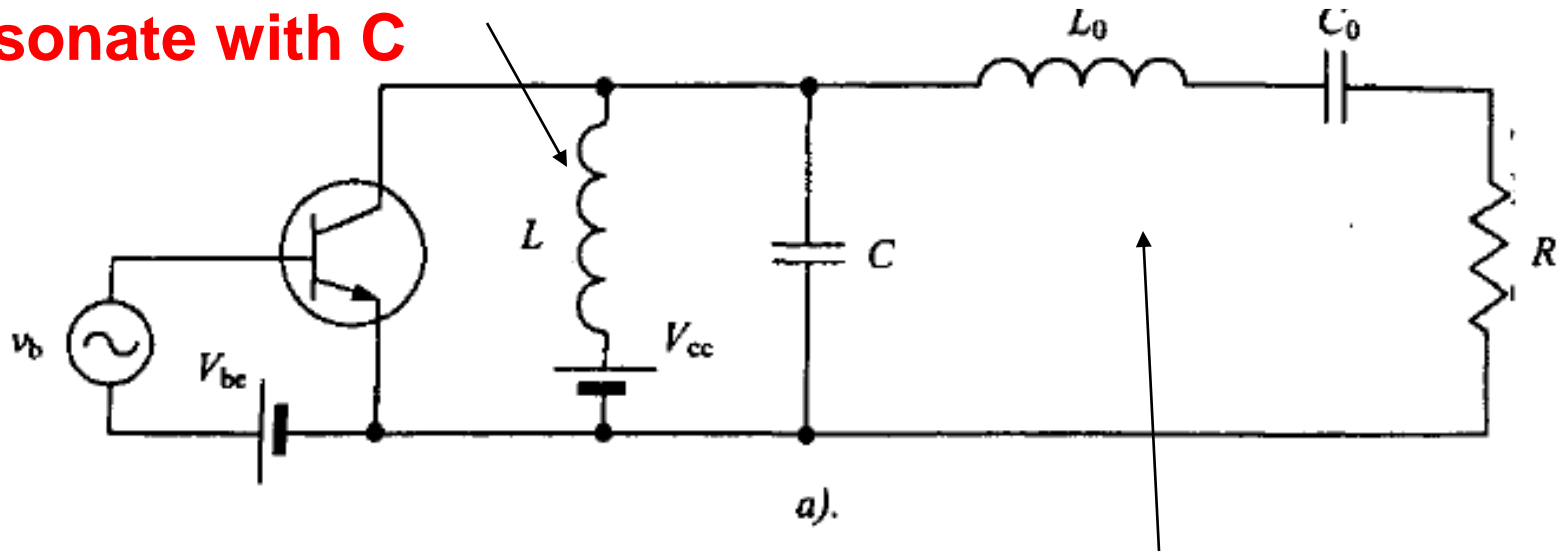
- their characteristic impedances are chosen to provide optimum inductive impedance seen by device at fundamental



- for three harmonic approximation, additional open circuit transmission line stub with 90-degree electrical length at third harmonic is required ( 1.5 GHz, 1.5 W, 90% )

# Another Style of Design for Class E

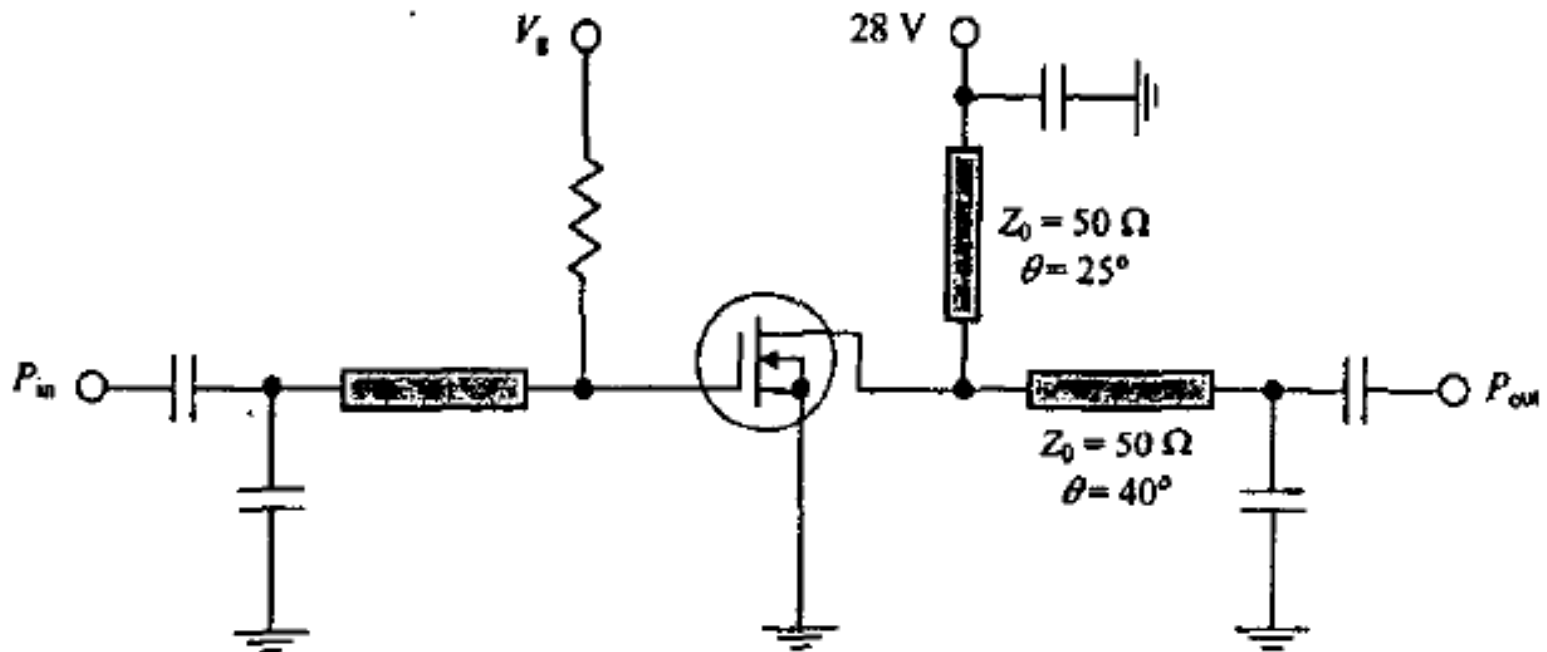
This is not an ideal choke, it is carefully tuned to resonate with C



This resonator is tuned to  $f_0$   
(not mistuned as in classical Class E)

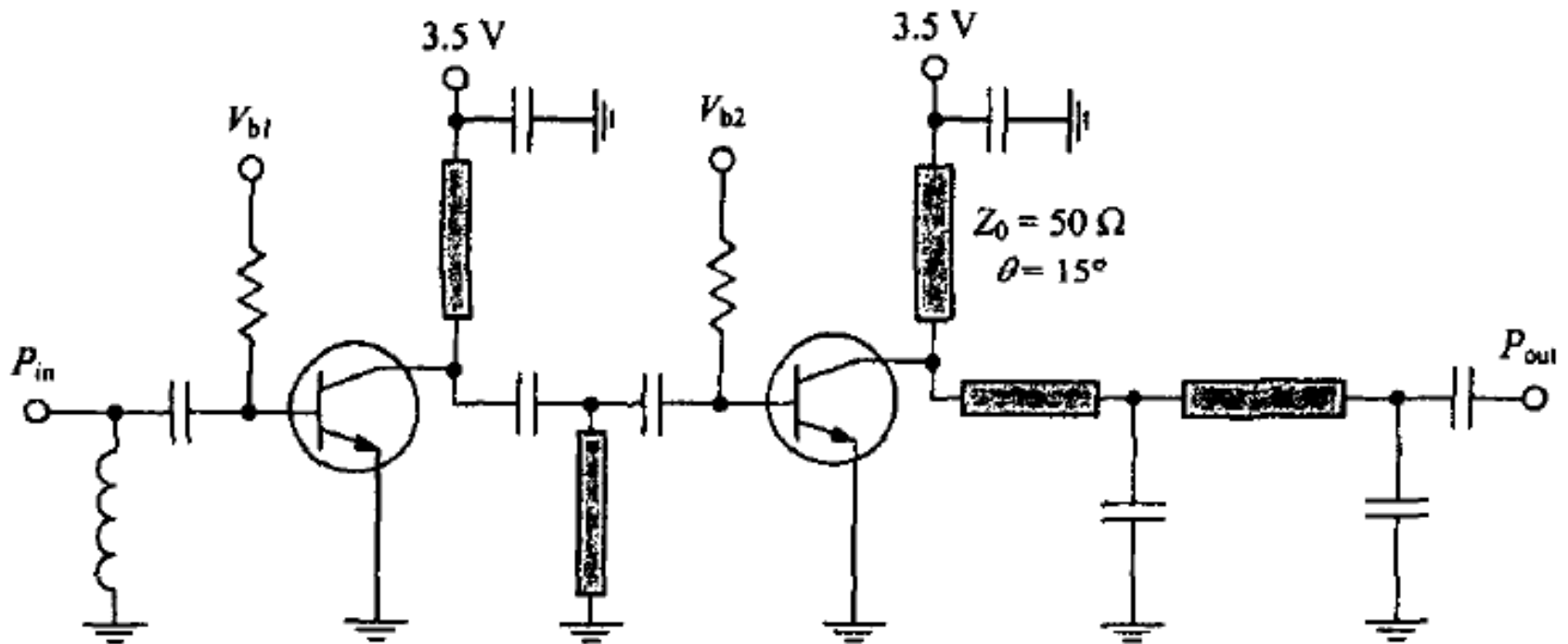
Approach of Grebbenikov and Jaeger

# Grebbenikov Design Implemented with Transmission Lines for LDMOS Switch

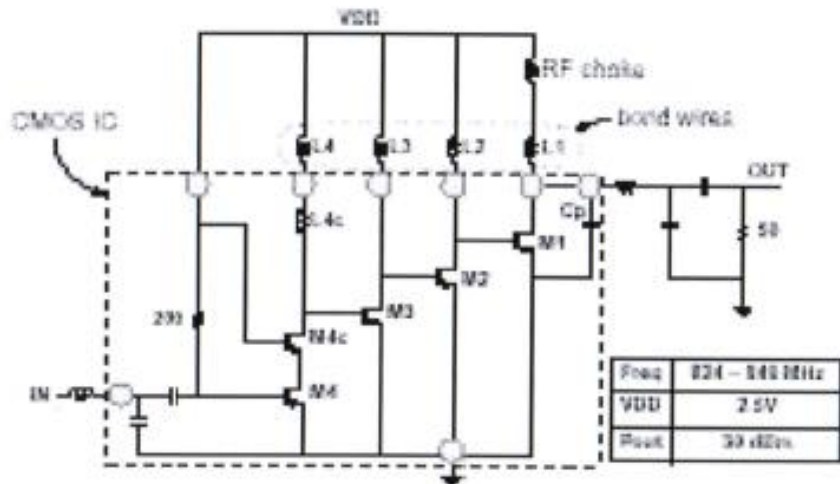




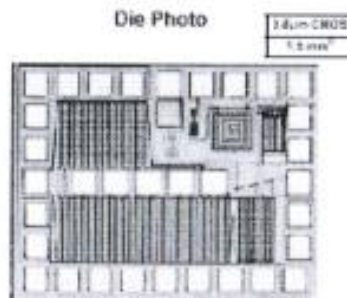
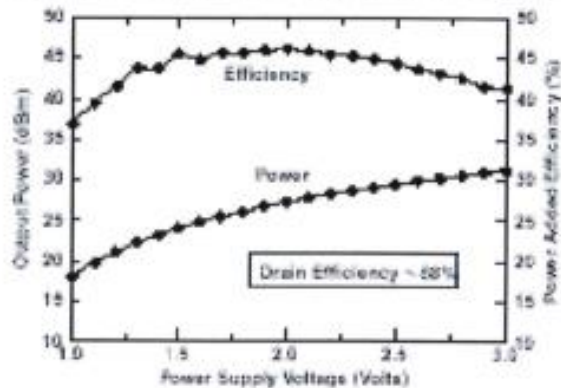
# Grebbenikov Design Implemented with Transmission Lines And HBTs for handsets



## CMOS



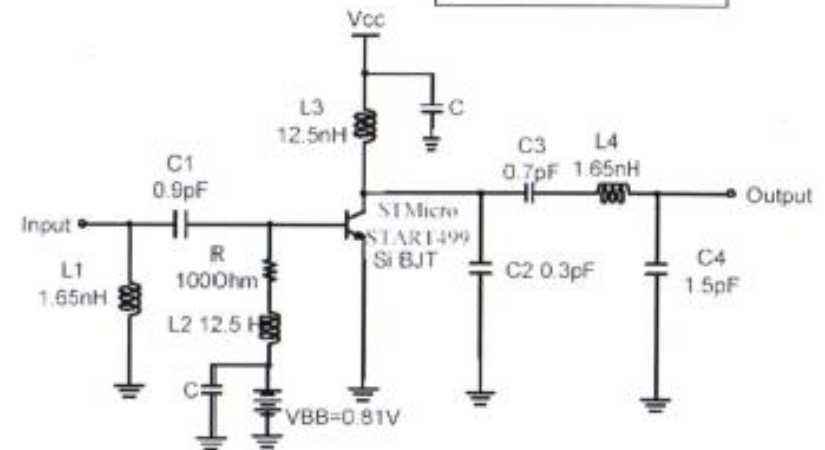
Measured Output Power and Efficiency



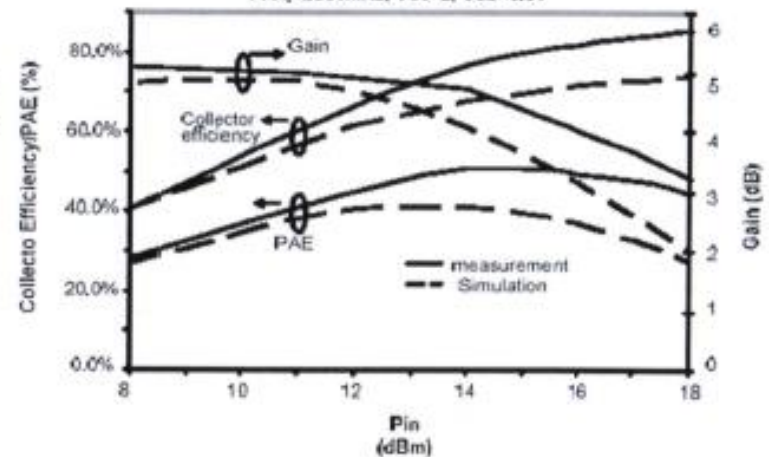
*D. Su et al, 1999*

## Class E Amplifiers Experimental Results

## Si BJT

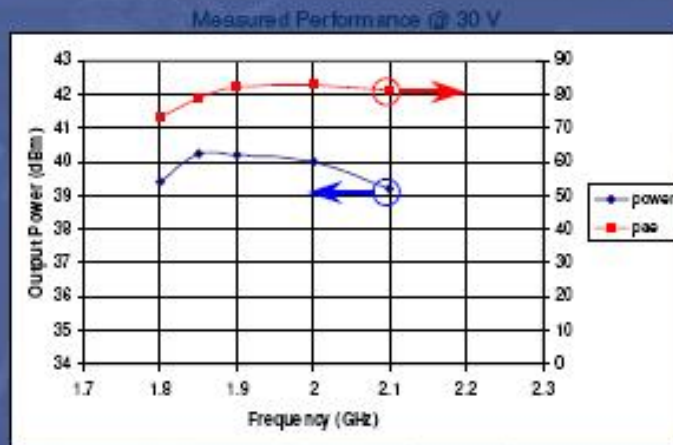


Class E Simulation vs. Measurements  
Freq=2360MHz, Vcc=2, Vbb=0.81

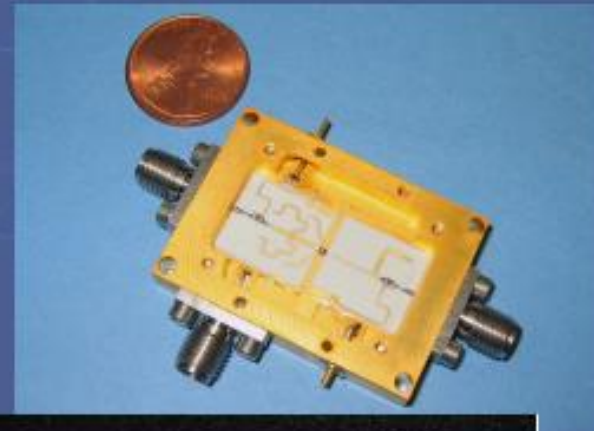


*Wang, Popp et al IMS2005*

# World Record 2.0 GHz High Efficiency GaN Amplifier



- Class E Hybrid amplifier
- $V_d = 30$  volts
- $50\Omega$  input/output
- $10\text{ W } P_{\text{OUT}}$ , **88% Drain Efficiency!**  
– 1.9 – 2.1 GHz!



**CREE** 

# Design Issues for Class E

1) Peak voltage across switch reaches  $3.6 \times V_{dd}$  for nominal design (so need a high breakdown device)

*In presence of output mismatch this can be  $5 \times V_{dd}$  or more (it can be risky without an isolator!)*

2) There is a maximum frequency possible to achieve class E operation, which depends on  $C_{out}$  and  $V_{dd}$

For Grebbenikov design, this is

$$f_{max} = 0.08 \cdot P_{out} / (C_{out} V_{dd}^2)$$

To maximize frequency need to minimize  $C_{out}$ . Chip-on-board could avoid package stray C (but need to get very good die attach for heat sinking)

*(If try to operate at  $f$  above  $f_{max}$ , can get  $V=0$  but not  $dV/dt=0$  when switch closes).*

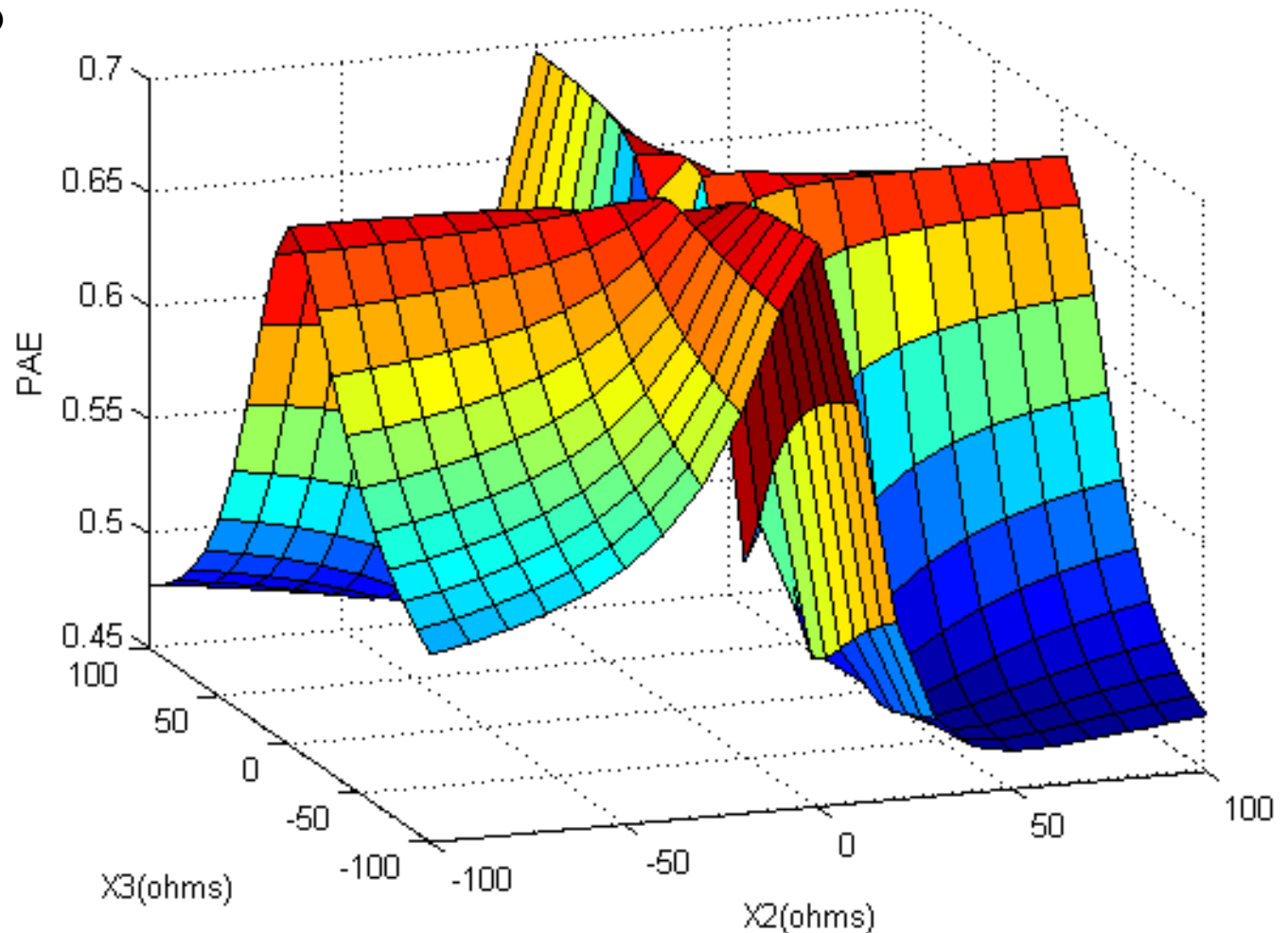
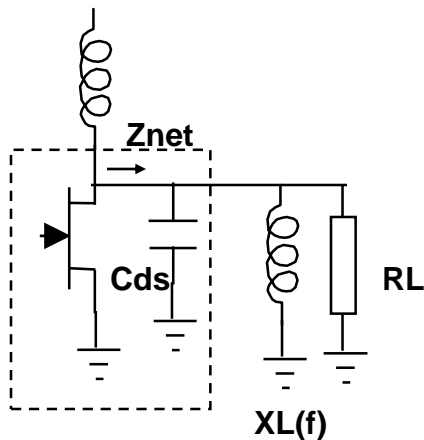
# Harmonic Load Tuning

Want to achieve high efficiency mode of operation  
Heavy compression - near switching mode

## *Simulated Efficiency vs Harmonic Load Reactance*

$X_2 = \text{Im}(Z_{\text{net}})$  at  $2f_0$

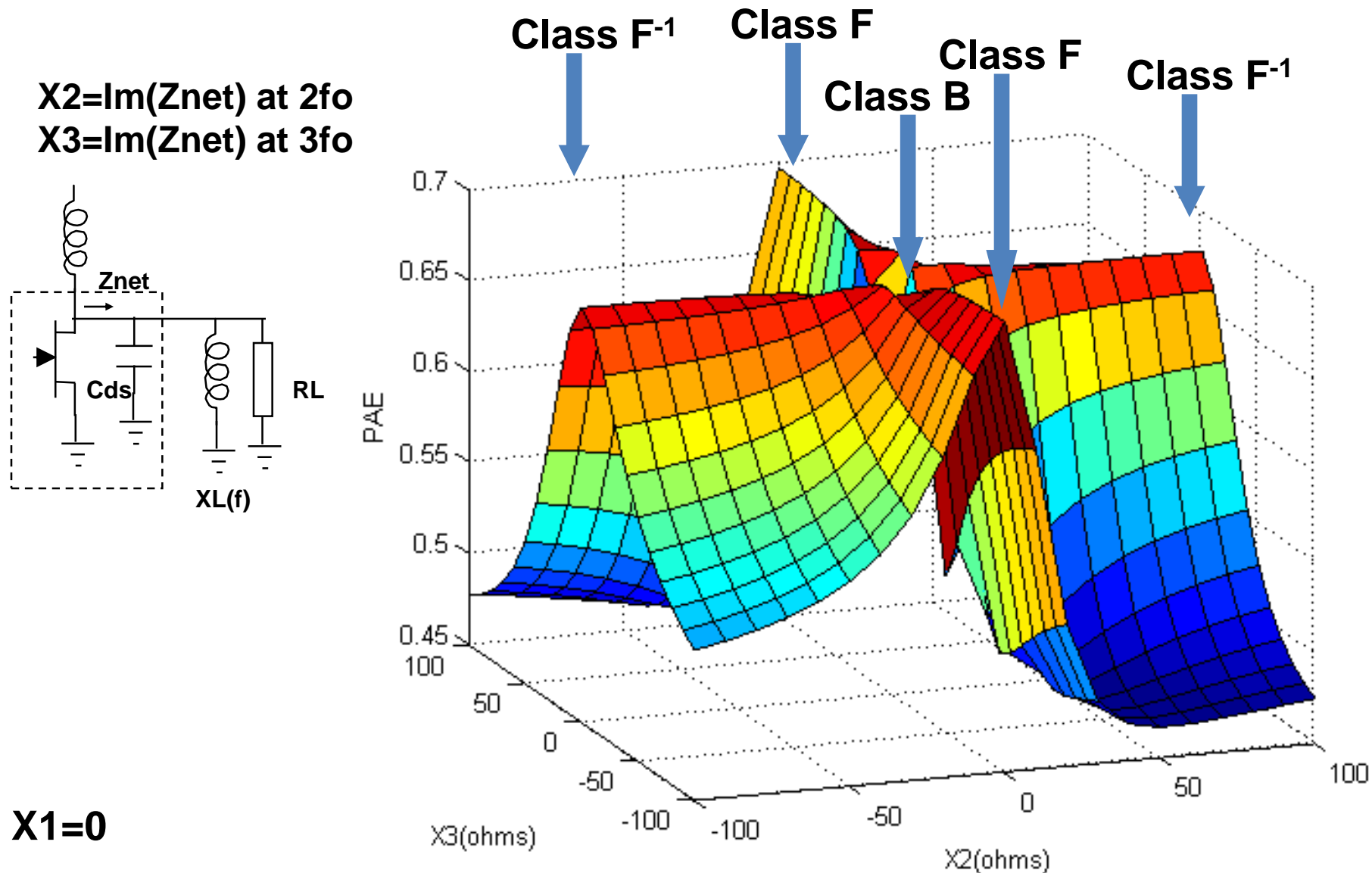
$X_3 = \text{Im}(Z_{\text{net}})$  at  $3f_0$



$X_1 = 0$

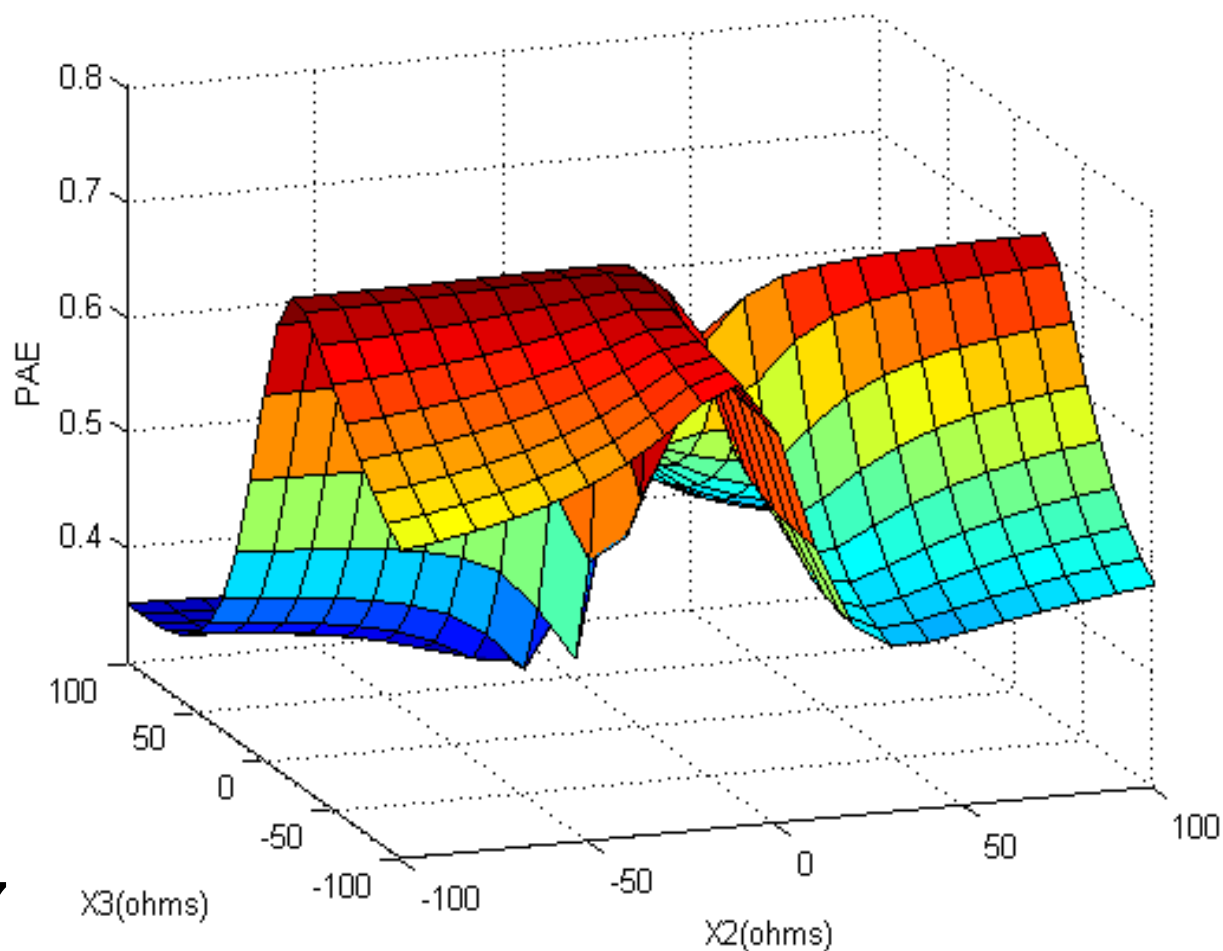
# Harmonic Load Tuning

## *Simulated Efficiency vs Harmonic Load Reactance*



# Harmonic Load Tuning

## *Simulated Efficiency vs Harmonic Load Reactance*



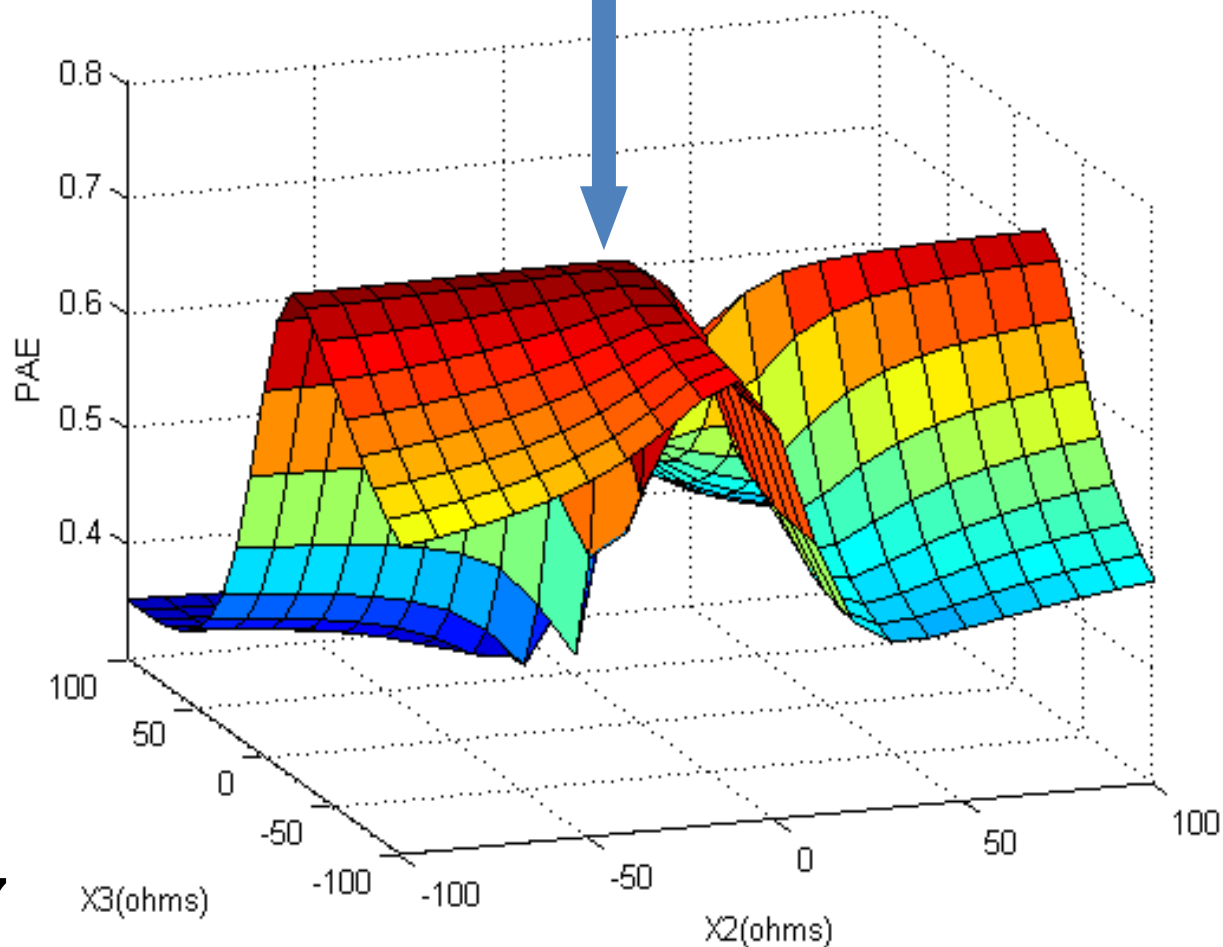
$$X1 = RL * 0.7$$



# Harmonic Load Tuning

## *Simulated Efficiency vs Harmonic Load Reactance*

**Class E**

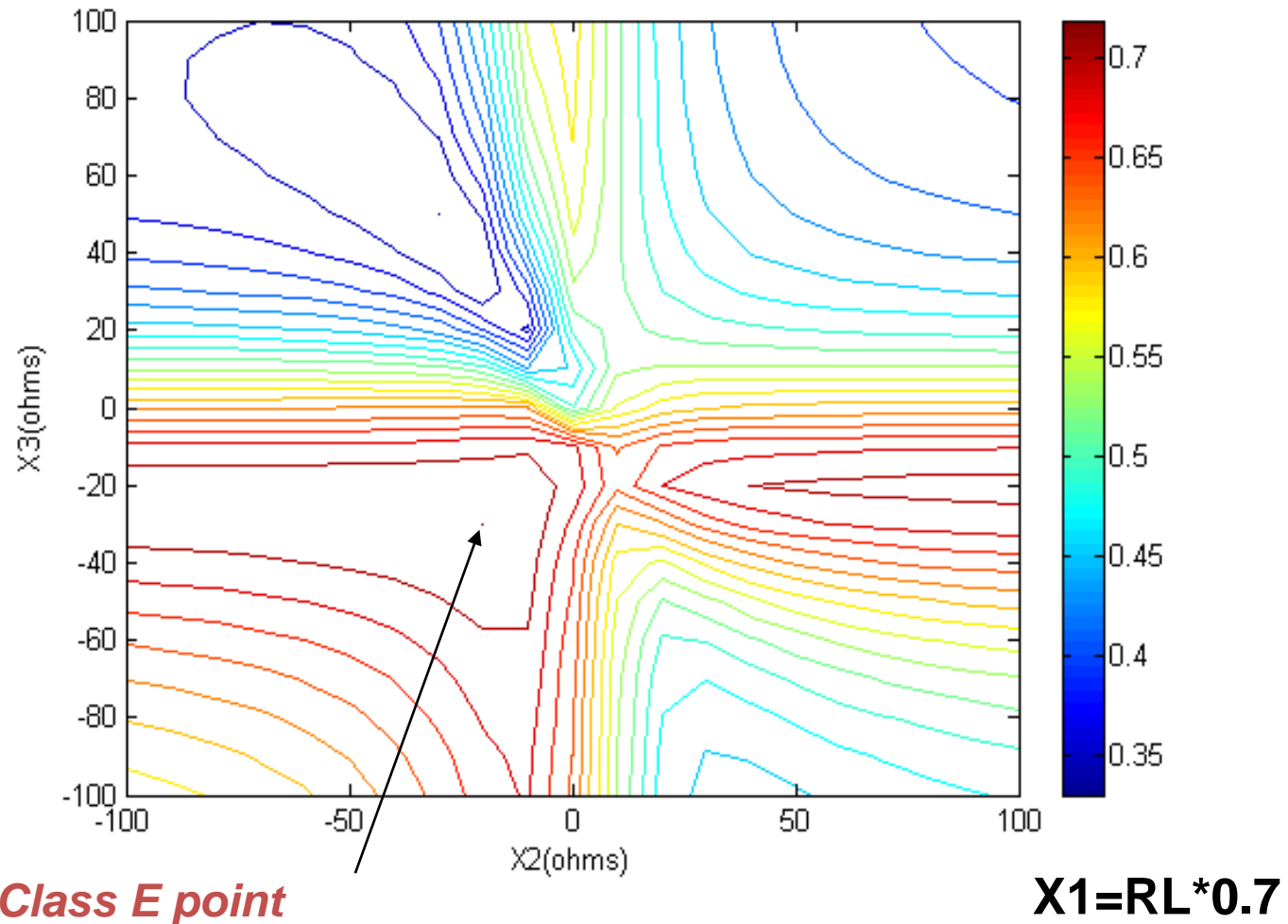


$$X1 = RL * 0.7$$



# Efficiency Optimization

Contours of PAE  
Vs  $X_2, X_3$  (fixed  $X_1$ )

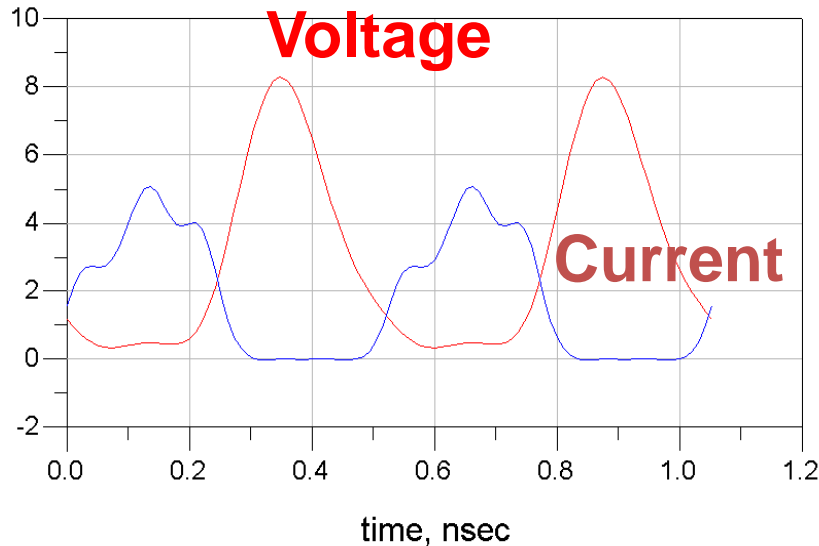


# Drain Voltage and Current Waveforms\* For Optimal Matching

Waveforms show "switching" behavior  
near zero during portion of cycle  
Requires even harmonics for voltage

- both are

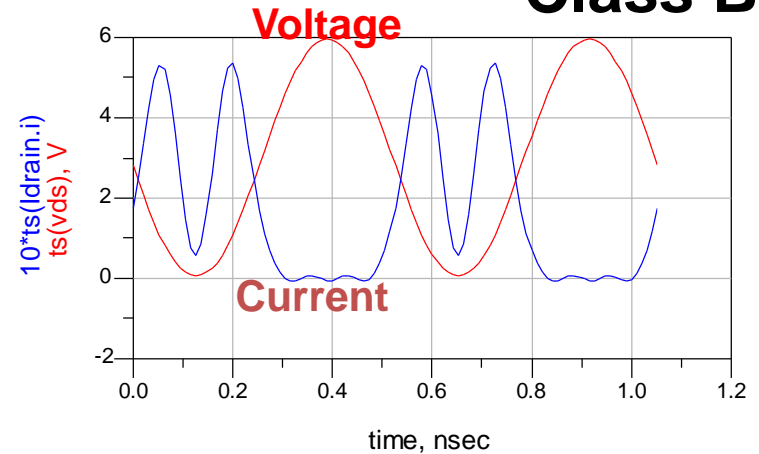
**Class B**



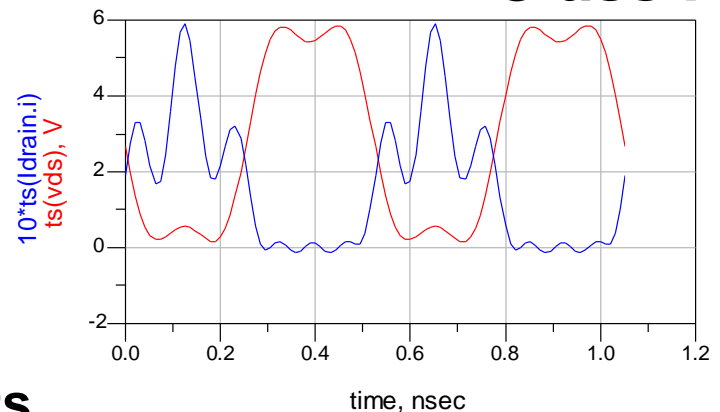
**Best: Overdriven Class "J"**  
Intermediate between Class E  
and Class F-1

**Representative simulated results**

***\*Current is through current generator only;  
Cds capacitive current is de-embedded***

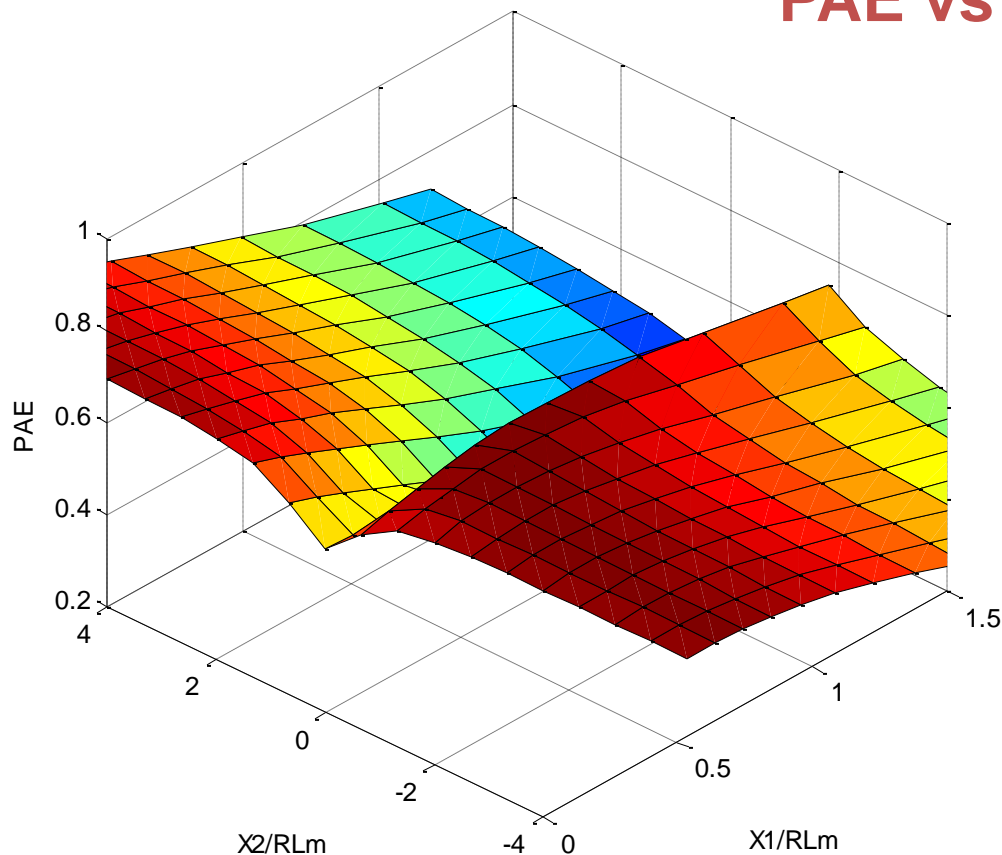


**Class F**

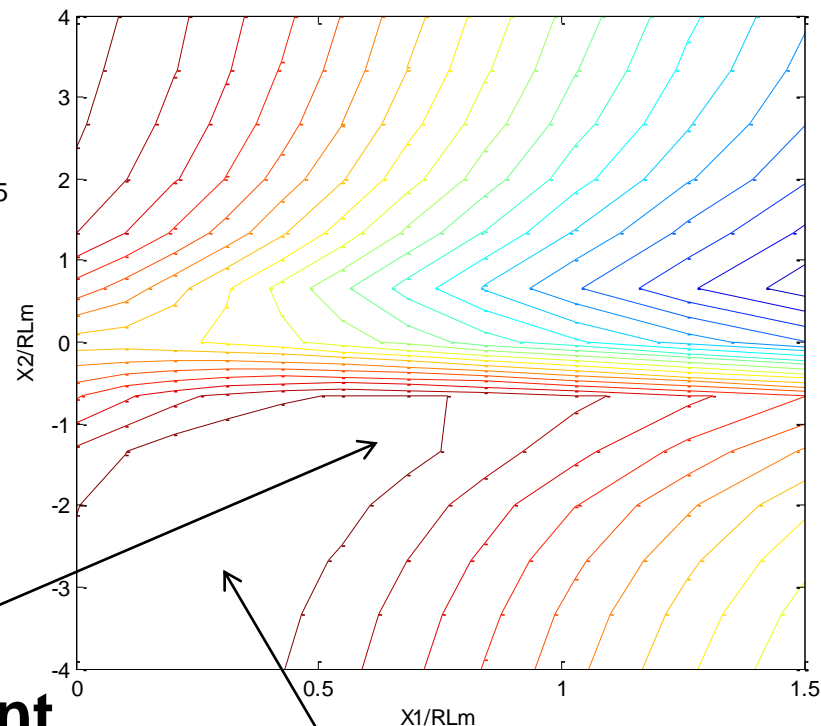


## PAE vs $X1/|ZL1|$ and $X2/|ZL1|$

For  $X3=0$   
short



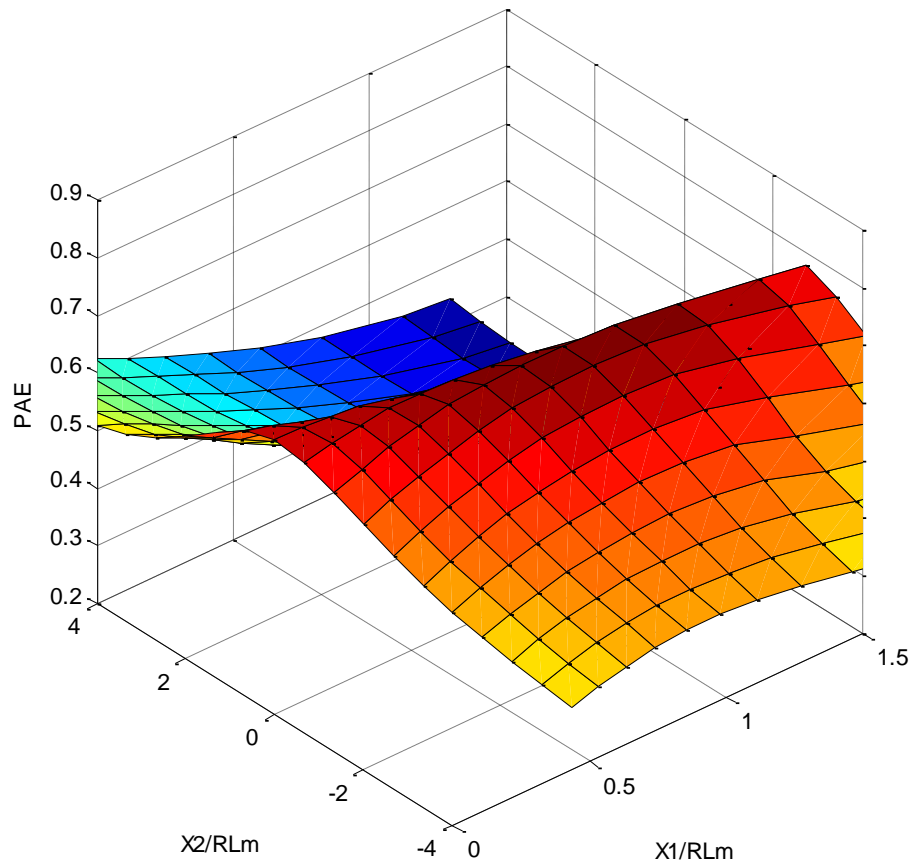
**Tradeoff**  
**Inductive ZL at  $f_0$**   
**With Capacitive Z at  $2f_0$**



**~Class E point**  
(if  $X3/magRL=0.96$  instead of 0)

**Class J region**

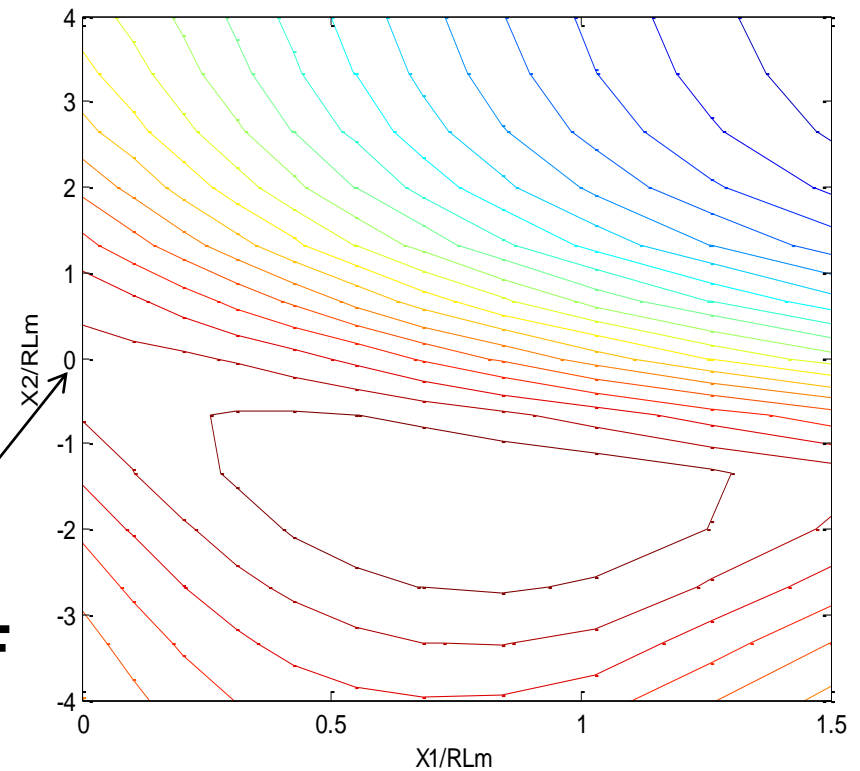
# PAE vs $X1/|ZL|$ and $X2/|ZL|$



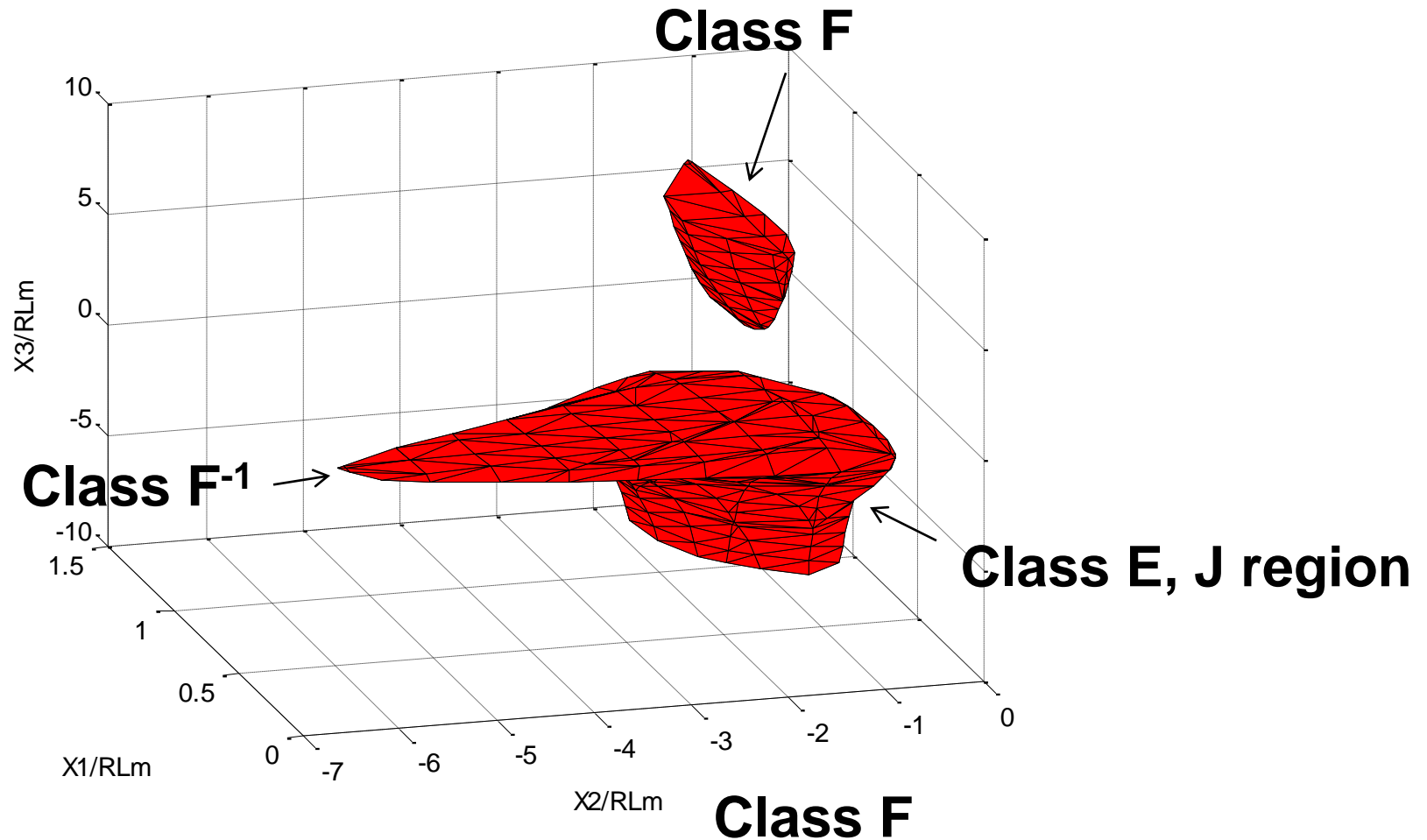
**Tradeoff**  
**Inductive ZL at  $f_o$**   
**With Capacitive Z at  $2f_o$**

**For  $X3=-6$**   
**~open**

**Class F**



## PAE vs $X1 / |ZL|$ , $X2 / |ZL|$ and $|X3| / |ZL|$



# Performance Dependence on Harmonic Content

- **Efficiency increases with harmonics**

Class F Harmonics	1 (class A)	2	3	4	5
Ideal drain efficiency %	50	71	82	87	91
Power output capability	0.125		0.144		0.151

- **Overdrive the amplifier to generate harmonics**



# Linearity Issues for High Efficiency Amplifier Modes

---

Switching mode amplifier output has constant envelope -  
determined by power supply, not by switch drive power  
=> used for phase modulated signals only

Class F amplifier can have acceptable linearity - but  $\eta$  drops

A key difficulty in optimizing efficiency for waveforms with time  
varying envelope is:

Need to minimize voltage across transistor,  
so want  $V_t = V_{\text{supply}} - V_{\text{rf}} = 0$

How to arrange this if  $V_{\text{rf}}$  varies?